

## P-Channel Enhancement Mode Power MOSFET

### Description

The PT F8ÚF€K uses advanced trench technology and design to provide excellent  $R_{DS(ON)}$  with low gate charge. It can be used in a wide variety of applications. It is ESD protected.

### General Features

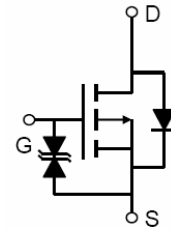
- $V_{DS} = -100V, I_D = -18A$   
 $R_{DS(ON)} < 100m\Omega @ V_{GS} = -10V$  (Typ: 85m $\Omega$ )
- Super high dense cell design
- Advanced trench process technology
- Reliable and rugged
- High density cell design for ultra low On-Resistance

### Application

- Power management in notebook computer
- Portable equipment and battery powered systems

**100% UIS TESTED!**

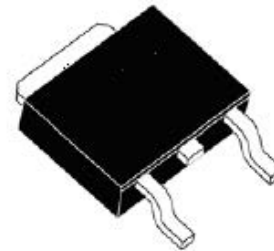
**100%  $\Delta V_{ds}$  TESTED!**



Schematic diagram



Marking and pin assignment



TO-252 top view

### Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
PT F8ÚF€K	PT F8ÚF€K	TO-252-2L	-	-	-

### Absolute Maximum Ratings ( $T_C = 25^\circ C$ unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	$V_{DS}$	-100	V
Gate-Source Voltage	$V_{GS}$	$\pm 20$	V
Drain Current-Continuous	$I_D$	-18	A
Drain Current-Continuous( $T_C = 100^\circ C$ )	$I_D(100^\circ C)$	-12	A
Pulsed Drain Current	$I_{DM}$	-72	A
Maximum Power Dissipation	$P_D$	70	W
Derating factor		0.56	W/ $^\circ C$
Operating Junction and Storage Temperature Range	$T_J, T_{STG}$	-55 To 150	$^\circ C$

### Thermal Characteristic

Thermal Resistance, Junction-to-Case (Note 2)	$R_{\theta jc}$	1.79	$^{\circ}\text{C/W}$
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### Electrical Characteristics ( $T_C=25^{\circ}\text{C}$ unless otherwise noted)

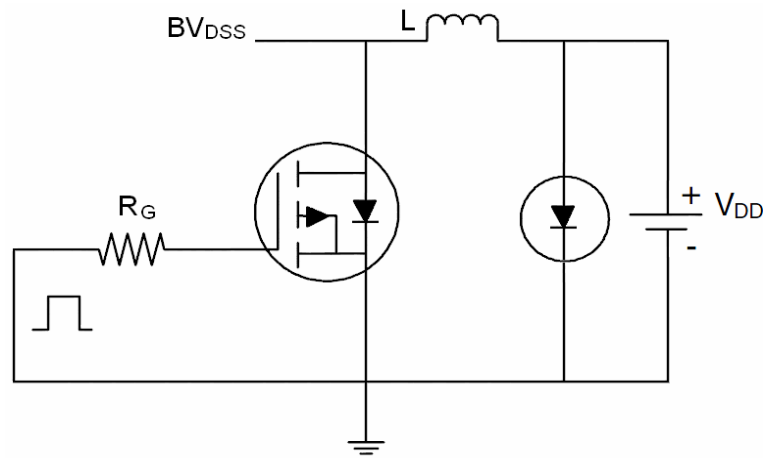
Parameter	Symbol	Condition	Min	Typ	Max	Unit
<b>Off Characteristics</b>						
Drain-Source Breakdown Voltage	$BV_{DSS}$	$V_{GS}=0V, I_D=-250\mu A$	-100	-	-	V
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS}=-100V, V_{GS}=0V$	-	-	1	$\mu A$
Gate-Body Leakage Current	$I_{GSS}$	$V_{GS}=\pm 20V, V_{DS}=0V$	-	-	$\pm 20$	$\mu A$
<b>On Characteristics (Note 3)</b>						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=-250\mu A$	-1	-1.9	-3	V
Drain-Source On-State Resistance	$R_{DS(on)}$	$V_{GS}=-10V, I_D=-16A$	-	85	100	m $\Omega$
Forward Transconductance	$g_{FS}$	$V_{DS}=-50V, I_D=-10A$	5	-	-	S
<b>Dynamic Characteristics (Note 4)</b>						
Input Capacitance	$C_{iss}$	$V_{DS}=-25V, V_{GS}=0V,$ $F=1.0\text{MHz}$	-	2100	-	PF
Output Capacitance	$C_{oss}$		-	590	-	PF
Reverse Transfer Capacitance	$C_{rss}$		-	140	-	PF
<b>Switching Characteristics (Note 4)</b>						
Turn-on Delay Time	$t_{d(on)}$	$V_{DD}=-50V, I_D=-16A$ $V_{GS}=-10V, R_{GEN}=9.1\Omega$	-	16	-	nS
Turn-on Rise Time	$t_r$		-	73	-	nS
Turn-Off Delay Time	$t_{d(off)}$		-	34	-	nS
Turn-Off Fall Time	$t_f$		-	57	-	nS
Total Gate Charge	$Q_g$	$V_{DS}=-80V, I_D=-16A,$ $V_{GS}=-10V$	-	61	-	nC
Gate-Source Charge	$Q_{gs}$		-	14	-	nC
Gate-Drain Charge	$Q_{gd}$		-	29	-	nC
<b>Drain-Source Diode Characteristics</b>						
Diode Forward Voltage (Note 3)	$V_{SD}$	$V_{GS}=0V, I_S=-10A$	-	-	-1.2	V
Diode Forward Current (Note 2)	$I_S$	-	-	-	-18	A
Reverse Recovery Time	$t_{rr}$	$T_J = 25^{\circ}\text{C}, I_F = -16A$ $di/dt = 100A/\mu s(\text{Note 3})$	-	88.3	-	nS
Reverse Recovery Charge	$Q_{rr}$		-	65.9	-	nC
Forward Turn-On Time	$t_{on}$	Intrinsic turn-on time is negligible (turn-on is dominated by LS+LD)				

### Notes:

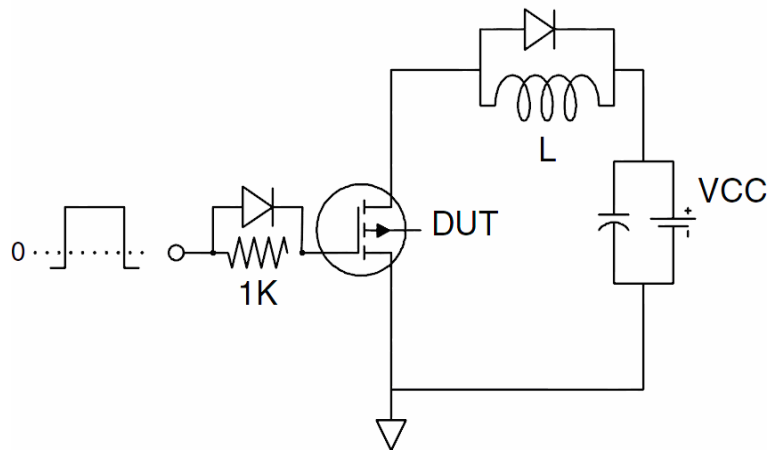
1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board,  $t \leq 10$  sec.
3. Pulse Test: Pulse Width  $\leq 300\mu s$ , Duty Cycle  $\leq 2\%$ .
4. Guaranteed by design, not subject to production
5. EAS condition:  $T_J=25^{\circ}\text{C}, V_{DD}=-50V, V_G=-10V, L=0.5\text{mH}, R_g=25\Omega$

### Test Circuit

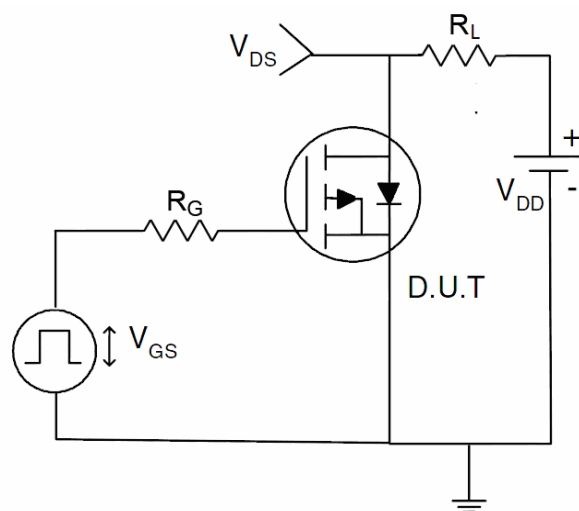
#### 1) $E_{AS}$ Test Circuit



#### 2) Gate Charge Test Circuit



#### 3) Switch Time Test Circuit



Typical Electrical and Thermal Characteristics (Curves)

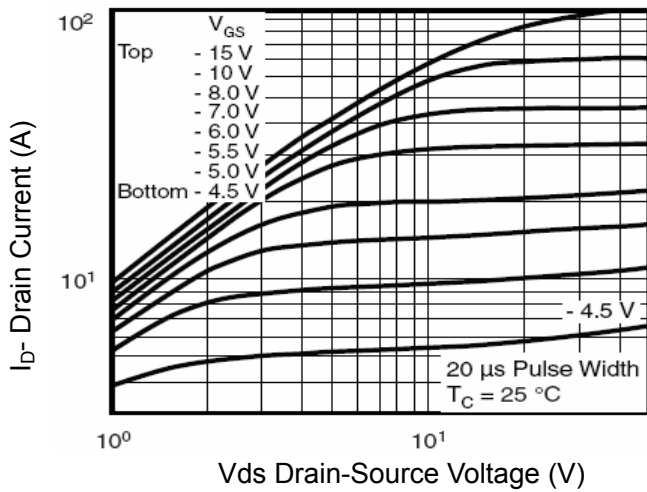


Figure 1 Output Characteristics

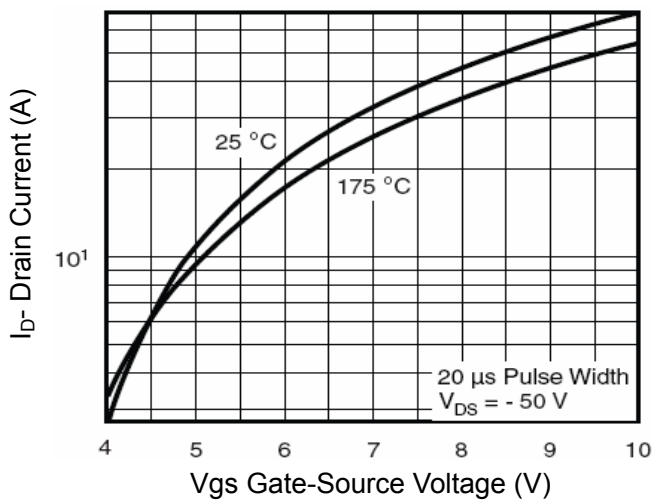


Figure 2 Transfer Characteristics

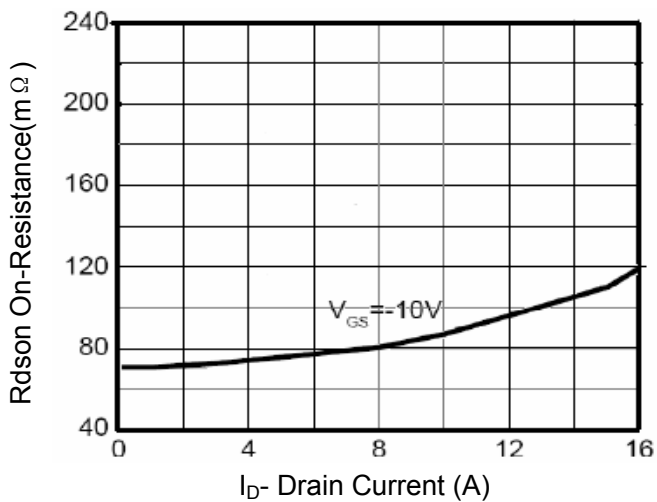


Figure 3  $R_{DS(on)}$ - Drain Current

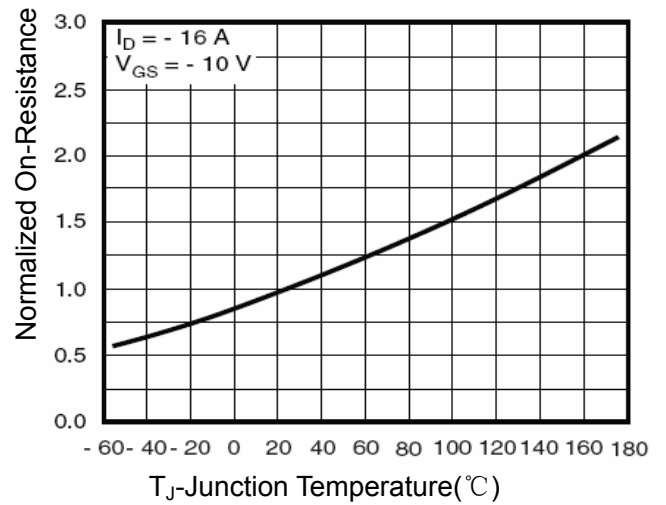


Figure 4  $R_{DS(on)}$ -Junction Temperature

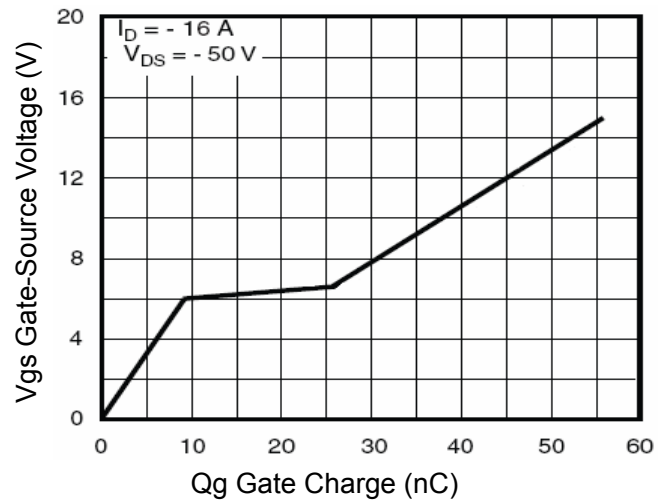


Figure 5 Gate Charge

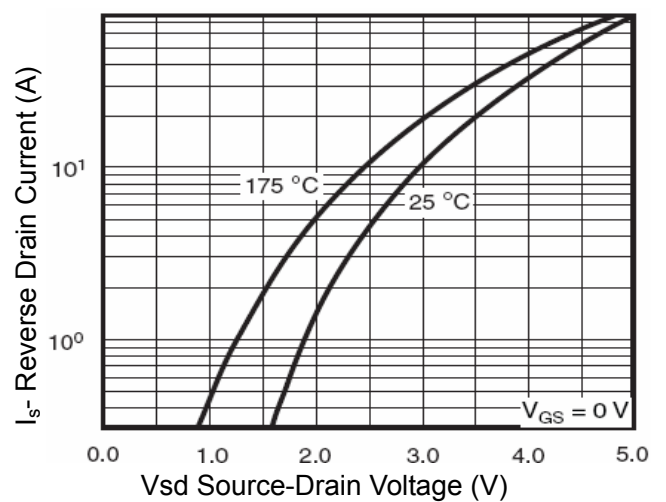


Figure 6 Source- Drain Diode Forward

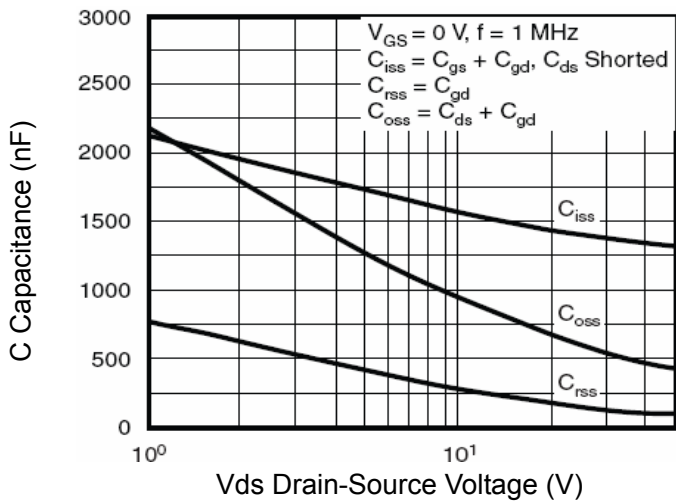


Figure 7 Capacitance vs Vds

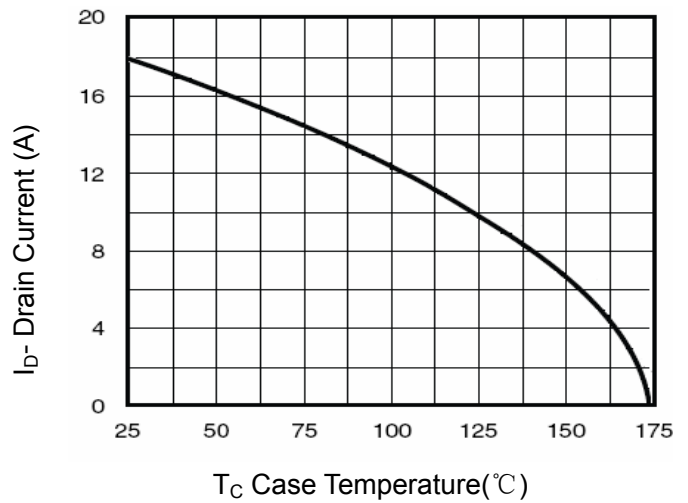


Figure 9 Drain Current vs Case Temperature

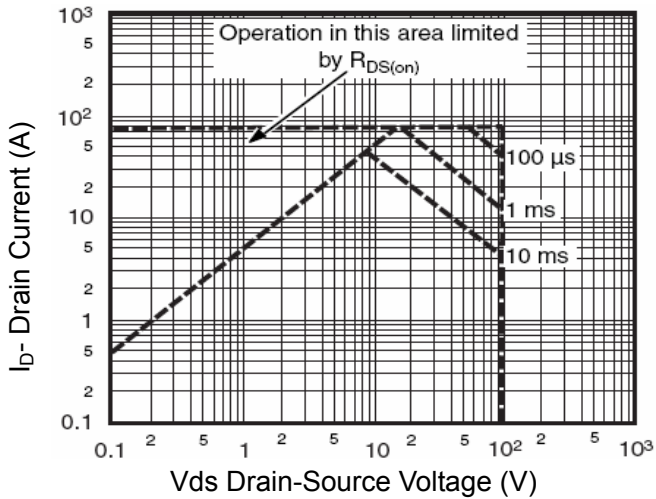


Figure 8 Safe Operation Area

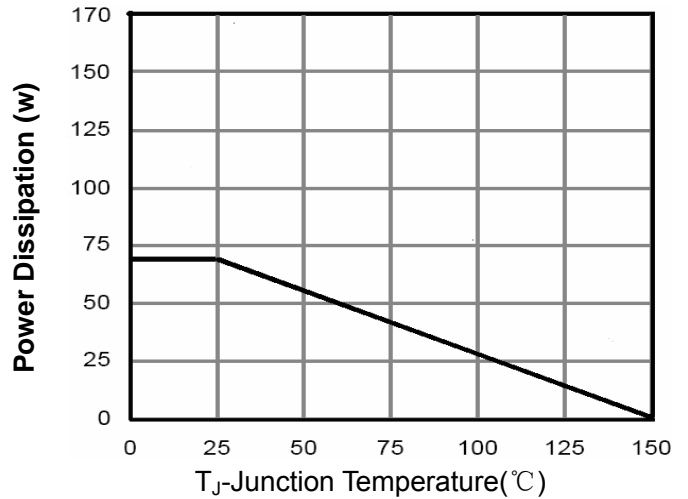


Figure 10 Power De-rating

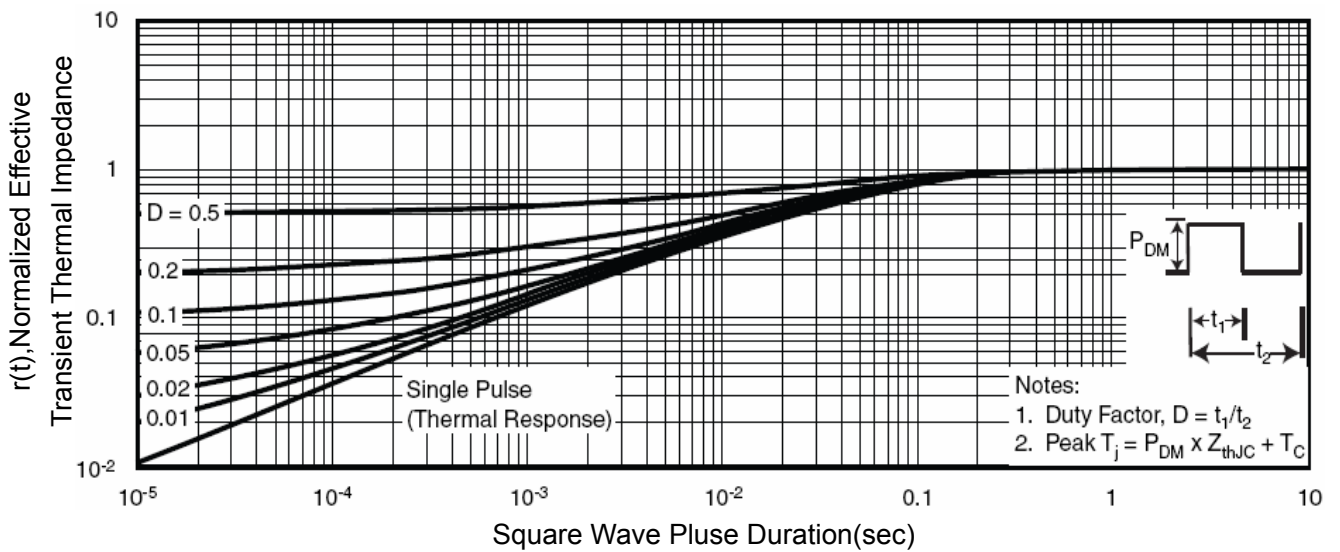
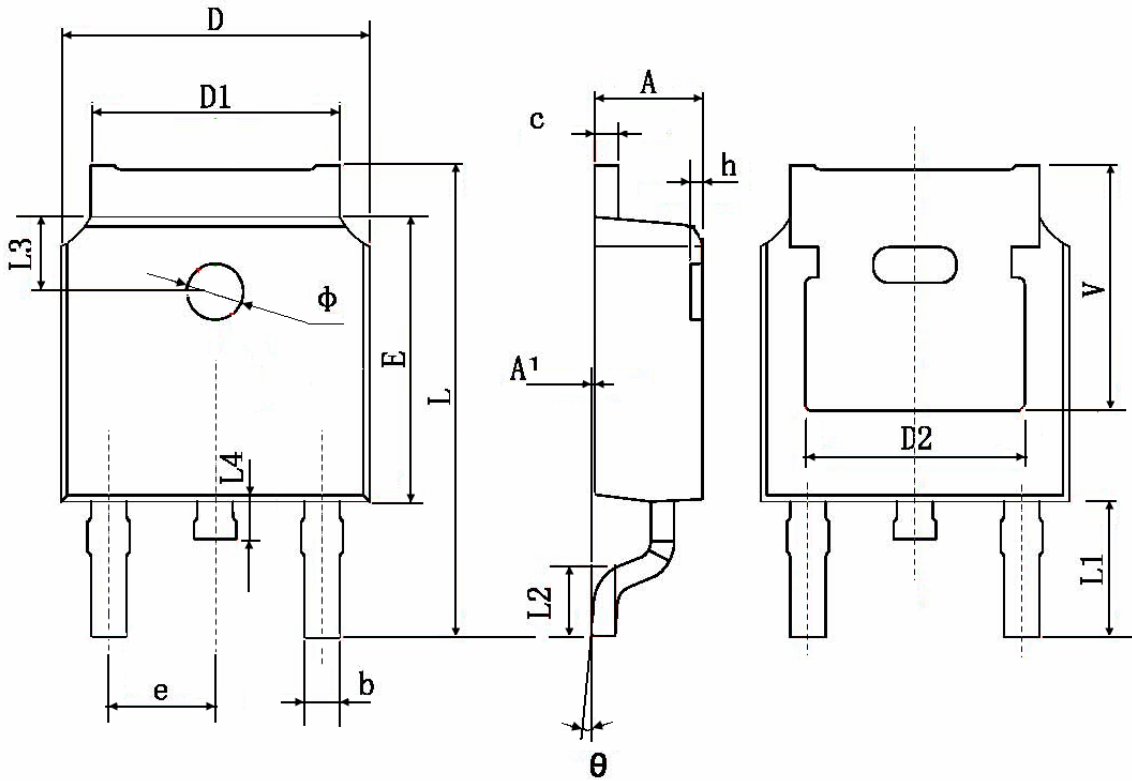


Figure 11 Normalized Maximum Transient Thermal Impedance

TO-252 Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	2.200	2.400	0.087	0.094
A1	0.000	0.127	0.000	0.005
b	0.660	0.860	0.026	0.034
c	0.460	0.580	0.018	0.023
D	6.500	6.700	0.256	0.264
D1	5.100	5.460	0.201	0.215
D2	0.483 TYP.		0.190 TYP.	
E	6.000	6.200	0.236	0.244
e	2.186	2.386	0.086	0.094
L	9.800	10.400	0.386	0.409
L1	2.900 TYP.		0.114 TYP.	
L2	1.400	1.700	0.055	0.067
L3	1.600 TYP.		0.063 TYP.	
L4	0.600	1.000	0.024	0.039
Φ	1.100	1.300	0.043	0.051
θ	0°	8°	0°	8°
h	0.000	0.300	0.000	0.012
V	5.350 TYP.		0.211 TYP.	